
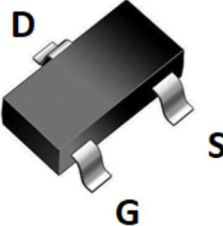
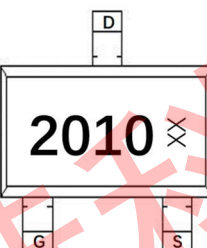
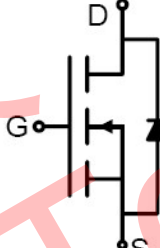




Description

N-channel Enhancement Mode Power MOSFET	
Features <ul style="list-style-type: none"> • 20V, 8A • $R_{DS(ON)} < 14m\Omega @ V_{GS} = 4.5V$ • $R_{DS(ON)} < 22.5m\Omega @ V_{GS} = 2.5V$ • Advanced Trench Technology • Excellent $R_{DS(ON)}$ and Low Gate Charge • Lead free product is acquired 	Application <ul style="list-style-type: none"> • Load Switch • PWM Application • Power management 
 <p>SOT-23-3L top view</p>	 <p>Marking and pin Assignment</p>
 <p>Schematic Diagram</p>	

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
2010	JMTJ100N02A	TAPING	SOT-23-3L	7inch	3000	180000

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	20	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current	$T_A = 25^{\circ}C$	8
		$T_A = 100^{\circ}C$	5
I_{DM}	Pulsed Drain Current ^{note1}	32	A
P_D	Power Dissipation	$T_A = 25^{\circ}C$	1.5
$R_{\theta JA}$	Thermal Resistance, Junction to Case	83.3	$^{\circ}C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^{\circ}C$



Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.75	1.2	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note2</small>	$V_{GS}=4.5V, I_D=8A$	-	11	14	m Ω
		$V_{GS}=2.5V, I_D=5A$	-	16	22.5	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=10V, V_{GS}=0V,$ $f=1.0MHz$	-	1000	-	pF
C_{oss}	Output Capacitance		-	182	-	pF
C_{rss}	Reverse Transfer Capacitance		-	164	-	pF
Q_g	Total Gate Charge	$V_{DS}=10V, I_D=4A,$ $V_{GS}=4.5V$	-	15	-	nC
Q_{gs}	Gate-Source Charge		-	2	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	5.2	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=10V,$ $I_D=4A, R_{GEN}=3\Omega,$ $V_{GS}=4.5V$	-	9	-	ns
t_r	Turn-on Rise Time		-	25	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	37	-	ns
t_f	Turn-off Fall Time		-	14	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	8	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=8A$	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$



Typical Performance Characteristics

Figure 1: Output Characteristics

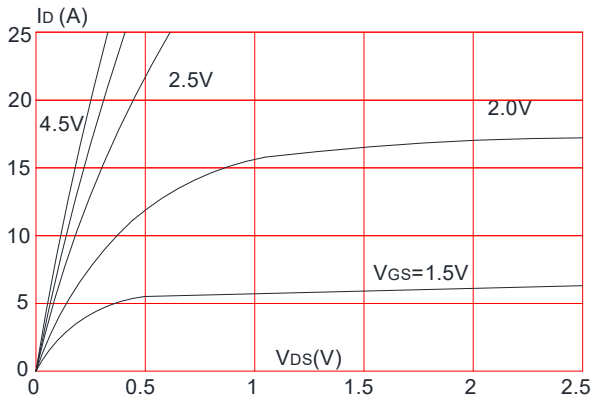


Figure 2: Typical Transfer Characteristics

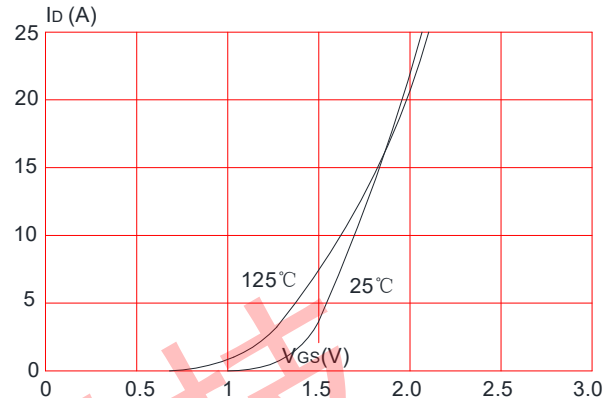


Figure 3: On-resistance vs. Drain Current

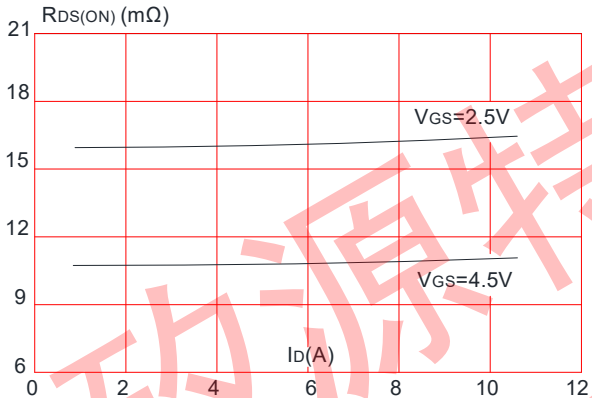


Figure 4: Body Diode Characteristics

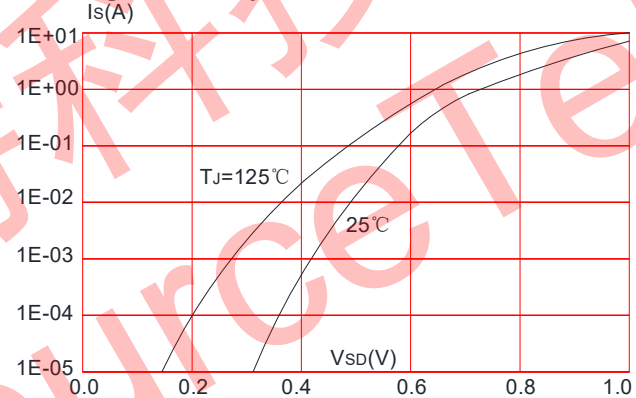


Figure 5: Gate Charge Characteristics

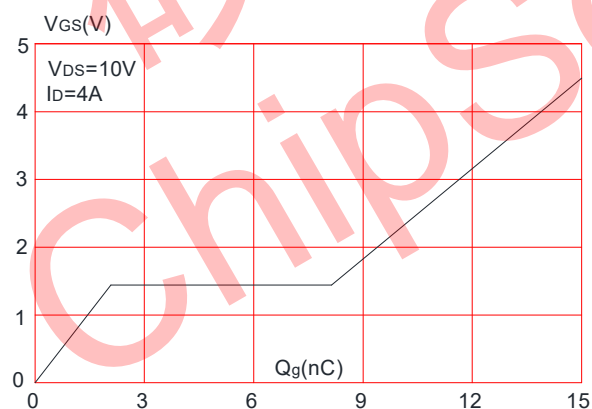


Figure 6: Capacitance Characteristics

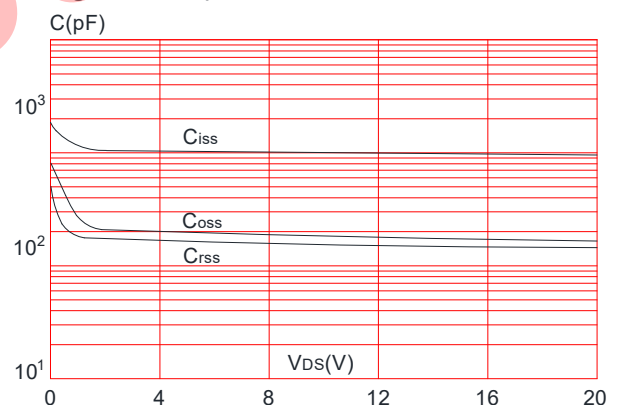




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

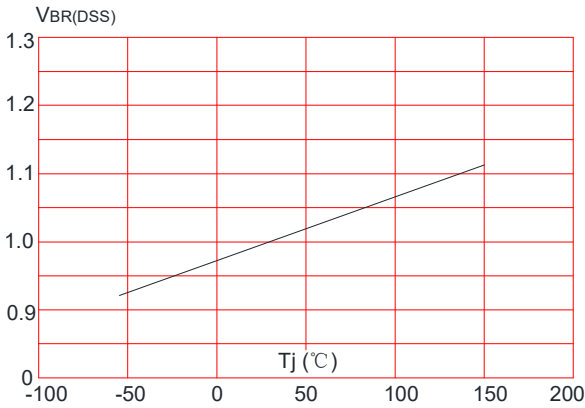


Figure 8: Normalized on Resistance vs. Junction Temperature

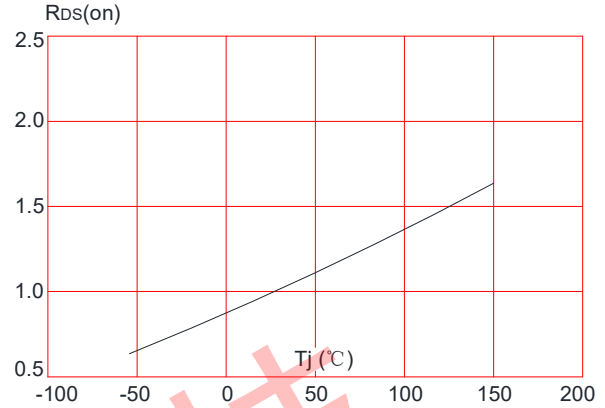


Figure 9: Maximum Safe Operating Area

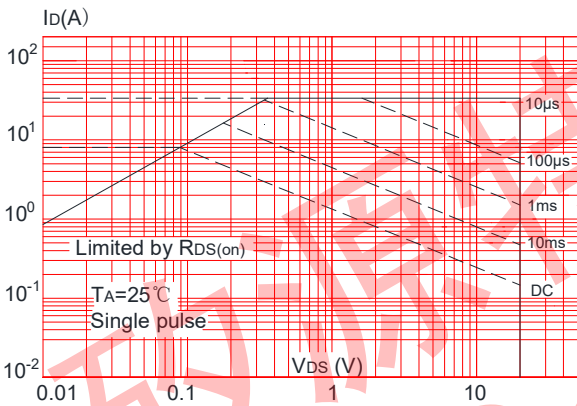


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

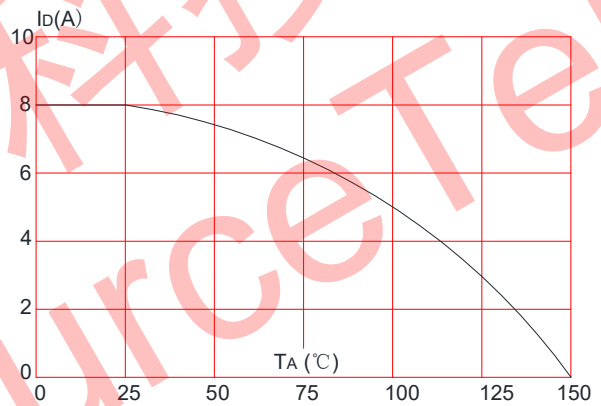
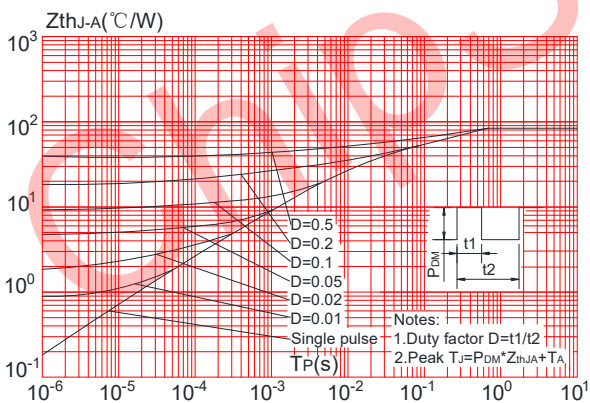


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





Test Circuit

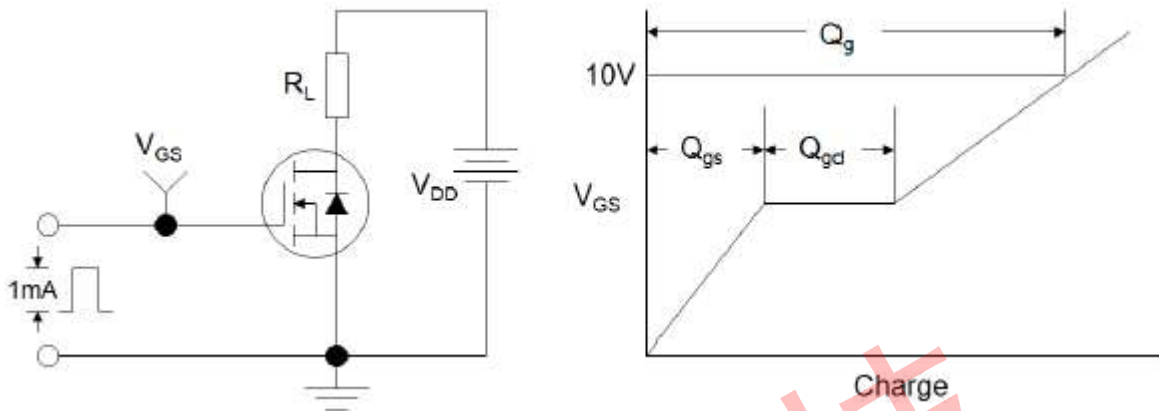


Figure1:Gate Charge Test Circuit & Waveform

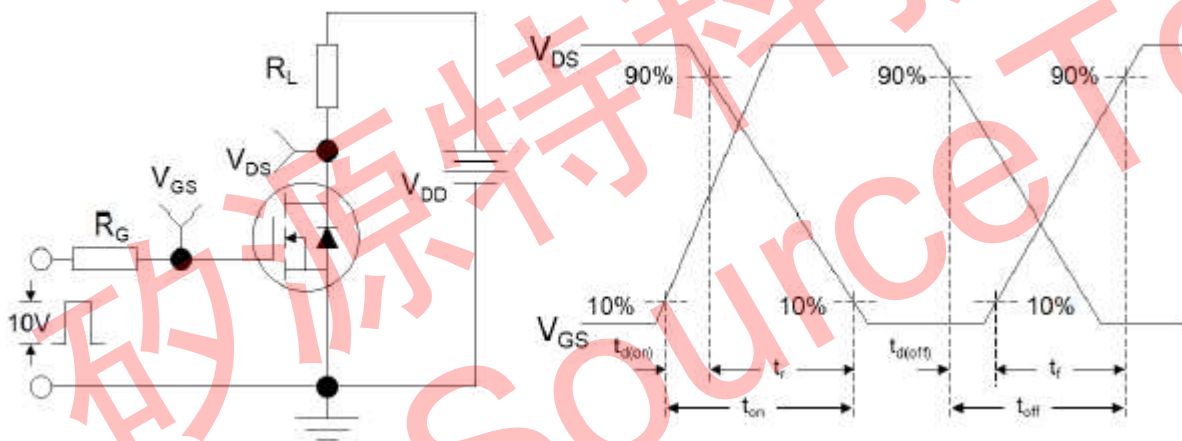


Figure 2: Resistive Switching Test Circuit & Waveforms

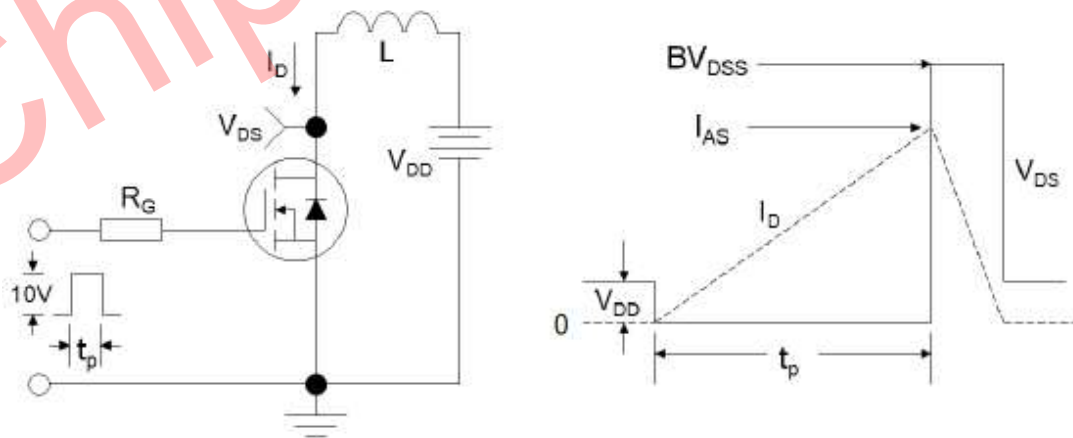
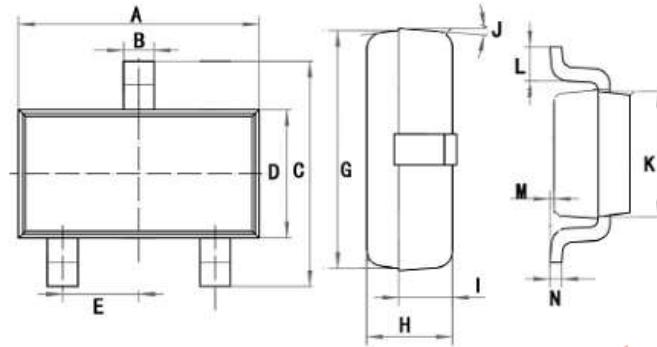


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



Package Mechanical Data-SOT-23-3L



A	2.90±0.1	E	0.950	J	7°	N	0.15 ^{+0.03}
B	0.4±0.01	G	2.85±0.1	K	1.550±0.1		
C	2.80±0.20	H	1.10±0.1	L	0.40		
D	1.60±0.1	I	0.70±0.1	M	0.05±0.03		

矽源特科技
ChipSourceTek